	Туре	L. #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1			USPAT; US-PGPU B; EPO; JPO; LERWENT; IBM_TDE	2003/ 03/20 14:58
2	BRS	L2	55199	electro-sptic\$ or electrooptic\$	USPAT; US-PGFU B; EFC; JPO; DERWENT; IBM_TDF	2003: 03/20 14:58
3	BRS	L3	703098	silicon	JSPAT; US-PGP' B; EPO JPO; DERWEN' ; IBM_TD	; 2003/ 03/20 T14:58
4	BRS	; L4	121471	semiconductor\$2 or semi-conductor\$2		03/20 03/20 T 15:00
15)	BRS	5 L:	5 9592	2 and 3	JPO;	PU 2003 03/2 NT 15:0

	Type	L #	Hits	Search Text	DBC	Time Stamp
6	BRS	6	121	a and 5	USPAT; US-PGPU B; EPG; JPG; DERWENT; IBM_TDB	2003/ 03/20 15:01
7	BRS	L7	357624	membrane\$2	USPAT; US-PGPU B; EPO; JPO; DERWENT; IBM_TDB	2003/ 03/20 15:01
8	BRS	L8	638	5 and 7	USPAT; US-PGPU B; EPO; JPO; DERWENT; IBM_TDE	2003/ 03/20 15:01
9	BRS	5 L9	41	1 and 8	USPAT; US-PGPUB; EPO JPO; DERWEN'; IBM_TD	; 2003/ 03/20 I15:05
10) BR	s Li	¹ 318125	mars or ((anti-reflect44 or antireflect\$4) near3 switch\$4)	USPAT; US-PGP B; EPO JPO; DERWEN; IBM_TI	U; 2003/ 03/20 T 15:08

	Туре	L #	Hits	Search Text	DBs Time Stamp
11	BRS	L1 1	2178	l not 6	USPAT; US-PGPU B; EPO; 2003 JPO; 03/20 DEFWENT 15:03 ; IBM_TDE
12	BRS	L1 2	248	2 and 3 and 7 and 10	USFAT; US-PGFU B; EP0; 2003/ JPO; 03/20 DERWENT 15:03 ; IBM_TDB
13	BRS	L1 3		12 not 9	USPAT; US-PGPU B; EPO; 2003/ JPO; 03/20 DERWENT 15:19 ; IBM_TDB
14	BRS	L1 4	2	goosen-keith\$.in.	USPAT; US-PGPU B; EPO; 2003/ JPO; 03/20 DERWENT 15:20 ; IBM_TDB
1.5	BRS	L1	3	goosen-k\$.in.	USPAT; US-PGPU B; EPO; 2003/ JFO; 03/20 DERWENT 15:20 ; IBM_TDB

	Туре	L #	Hits	Search Text	DBs	Time Stamp
16	BRS	L1 6	104	goossen-keith\$.in.	USPAT; US-PGPU B; EPC; JPO; DERWENT; IBM_TIP	2003/ 2003/20 15:20
17	BRS	L1	15	10 and 16	USPAT; US-PGPUB; EPO; JPO; DERWEN; ; IBM_TD	; 2003/ 03/20 [15:20

	Doc	umer	ı <u>t</u> I	D	1	Source	Issu e Date	ge	Title	Current OR	Current XRef
	US 2002 A 1	2010	990	4		U S -		13	Fast attenuator	359/291	359/290 ; 359/292 : 137/831
	US	4203	3128	3 A	<u>[:</u>	U S P A T	1980 0513		Electrostatically deformable thin silicon membranes	331/156	; 257/415 ; 257/531 ; 257/E29 .324; 361/231 ; 361/233 .4; 73/77
3	US	523	153	2 F	<u>.</u>	P	100		Switchable resonant filter for optical radiation	359/295	359/39; 359/578; 359/58; ; 359/58;
	US	550	691	9 2	Α.[: 	J S 199 P 040 A	6 9 1	Conductive membrane optical modulator	385/1	385/2; 385/23
- -	US	551	.027	.77	A	[]	U S 199 P 042 T	6 3	Surface treatment for silicon substrates	438/70	134/1. 7; 438/97 359/29
б	US	594	1315	5 5	Α.		U S 199 A 082	99	Mars optical modulators	359/24	; 359/29

	Document ID 1	u	Issu e Date	ge	Title	Current OR	Current XRef
ij	US 5943155 A	E F.	1999 0824	13	Double poly mechanical antireflection switch (MARS) device for optical modulators		
ē	US 5943159 A		1999 0824	1	Micro-mechanical, anti-reflection, switched optical modulator array and fabrication method	359/295	359/230 ; 359/231 ; 359/318 359/223
9	US 5949571 A [USPAT	1999	13	Mars optical modulators	359/291	; 359 224 ; 359 224
10	US 6337753 B1	Ü S S P A T	2002 0108	8	Optical power equalizer	359/124	359/291
11	US 6462858 B1	U S F A	, 2002 1008		Fast attenuator	359/290	359/237 ; 359/291 ; 359/295 ; 359/847
12	US 6519073 B1		2 ⊃üU.	3 1	Micromechanical modulator and method for fabricating the same	s 359/290	359,248); 359/291